



30V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C		
30V	$5.5 \text{m}\Omega$ @ $V_{GS} = 10V$	75A		
	$8.5 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	50A		

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- **Engine Management Systems**
- **Body Control Electronics**
- DC-DC Converters

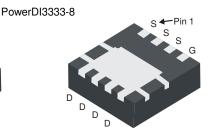
Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (Test in Production) -Ensures More Reliable and Robust End Application
- Low $R_{DS(ON)}$ Ensures On-State Losses are Minimized
- Excellent Q_{qd x} R_{DS(ON)} Product (FOM)
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note4)

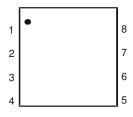
Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

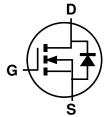




Bottom View







Equivalent Circuit

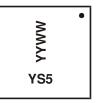
Ordering Information (Note 5)

Top View

Part Number		Case	Packaging		
DMTH3004LFGQ-7		PowerDI3333-8	2,000/Tape & Reel		
DMTH3004LFGQ-13		PowerDI3333-8	3,000/Tape & Reel		
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.				

- 2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



YS5 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	30	V	
Gate-Source Voltage	V_{GSS}	±16	V	
Continuous Drain Current (Notes 7 & 10) V _{GS} = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	Ι _D	75 52	А
Continuous Drain Current (Note 6) V _{GS} = 10V	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	Ι _D	15 10	Α
Maximum Continuous Body Diode Forward Current (Note 6)	Is	3	Α	
Pulsed Drain Current (100μs Pulse, Duty Cycle = 1%)	I _{DM}	250	Α	
Pulsed Body Diode Forward Current (100µs Pulse, Duty Cyc	I _{SM}	250	Α	
Avalanche Current, L=0.3mH	I _{AS}	27	A	
Avalanche Energy, L=0.3mH	E _{AS}	110	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 7)	$T_{C} = +25^{\circ}C$	P_{D}	50	W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	3	°C/W	
Total Power Dissipation (Note 6)	P_{D}	2.5	W	
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	60	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

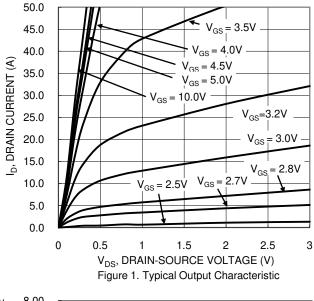
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μA	V _{DS} = 24V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	•						
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		-	4.1	5.5	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	6.2	8.5	11122	$V_{GS} = 4.5V, I_D = 7A$	
Diode Forward Voltage	V _{SD}	-	0.7	1	V	V _{GS} = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	-	2370	-		V _{DS} = 15V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	C _{oss}	-	1360	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	240	-			
Gate Resistance	R_{g}	-	0.6	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	20	-			
Total Gate Charge (V _{GS} = 10V)	Qq	-	44	-			
Gate-Source Charge	Q _{qs}	-	7	-	nC	$V_{DS} = 15V, I_D = 20A$	
Gate-Drain Charge	Q _{gd}	-	8	-			
Turn-On Delay Time	t _{D(ON)}	-	6.2	-			
Turn-On Rise Time	t _R	-	4.3	-		$\begin{aligned} V_{DD} &= 15 V, \ V_{GS} = 10 V, \\ R_{L} &= 0.75 \Omega, \ R_{g} = 3 \Omega, \ I_{D} = 20 A \end{aligned}$	
Turn-Off Delay Time	t _{D(OFF)}	-	21	-	ns		
Turn-Off Fall Time	t _F	-	8	-			
Body Diode Reverse Recovery Time	t _{RR}	-	25	-	ns	1 45A 41/-14 500A/	
Body Diode Reverse Recovery Charge	Q _{RR}	-	37	-	nC	$I_F = 15A$, di/dt = 500A/ μ s	

- 6. R_{0JA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. R_{0JC} is guaranteed by design while R_{BJA} is determined by the user's board design.

 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.
- 10. Package limited.







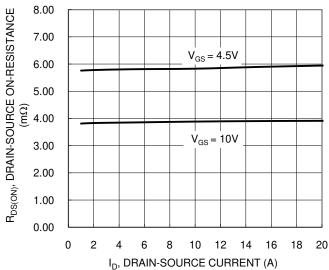


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

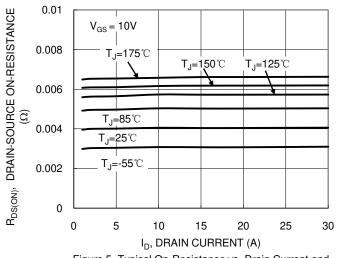


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

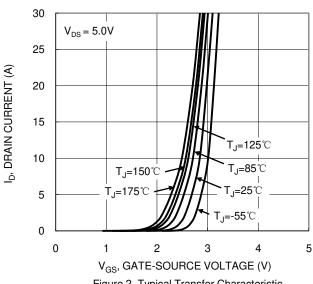


Figure 2. Typical Transfer Characteristic

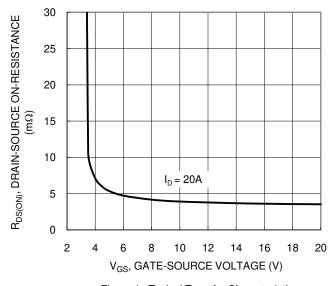


Figure 4. Typical Transfer Characteristic

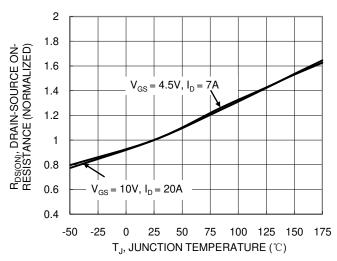


Figure 6. On-Resistance Variation with Temperature



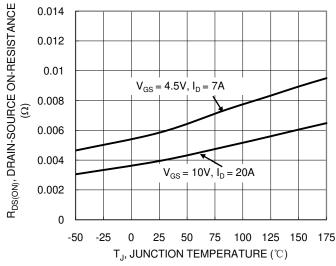


Figure 7. On-Resistance Variation with Temperature

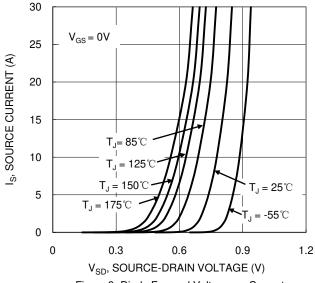


Figure 9. Diode Forward Voltage vs. Current

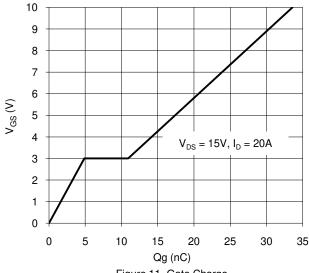


Figure 11. Gate Charge

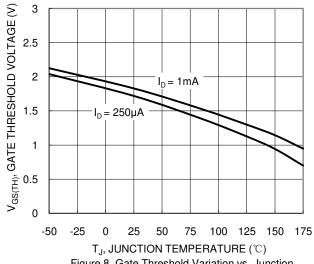
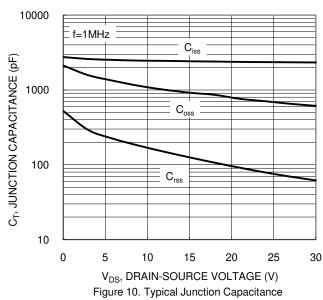
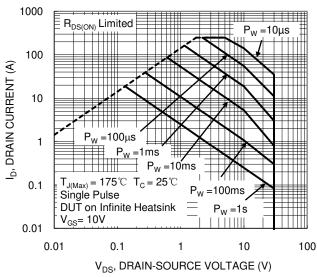


Figure 8. Gate Threshold Variation vs. Junction Temperature







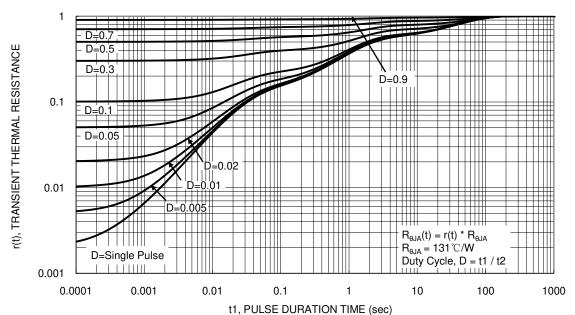


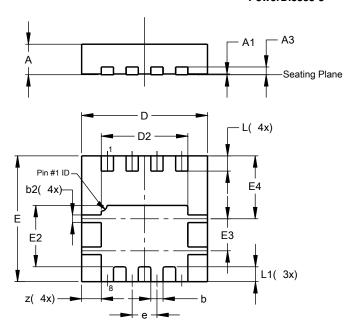
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

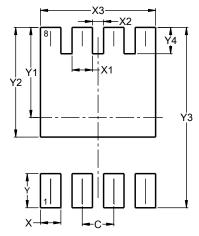


PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A 3	-	-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
E	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	_	_	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
Z	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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